

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Extended temperature range T<sub>i</sub> = 175 °C
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- Trench MOSFET technology
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
ID	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	-	11	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C		-	-	15	W
Static chara	cteristics		I				
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4 A; T <sub>j</sub> = 25 °C		-	42	56	mΩ



# 5. Pinning information

Table 2	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		D
2	D	drain		
3	G	gate		G ↓ ↓ ↓ ↓ ↓
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	s s
7	D	drain		017aaa255
8	S	source		

# 6. Ordering information

#### Table 3. Ordering information

Type number Package			
	Name	Description	Version
BUK6D56-60E		plastic, leadless thermal enhanced ultra thin small outline package; 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
BUK6D56-60E	4V

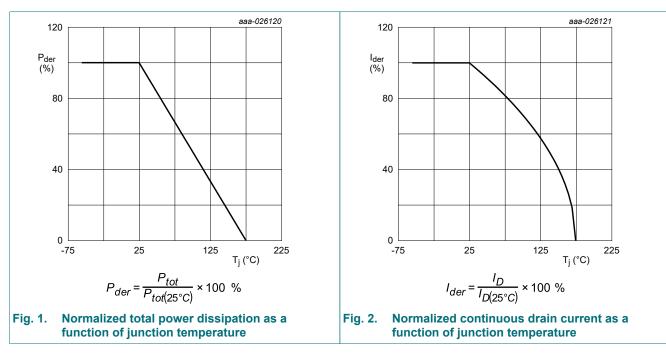
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

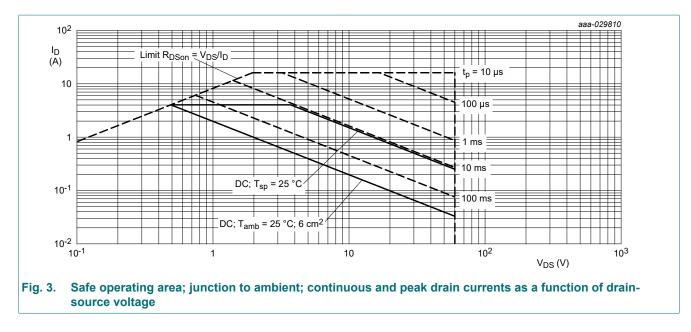
Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
ID	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	11	А
		V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 100 °C		-	8	А
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	4	А
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	44	А
P <sub>tot</sub> total power di	total power dissipation	T <sub>sp</sub> = 25 °C		-	15	W
		T <sub>amb</sub> = 25 °C	[1]	-	2	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	diode					
I <sub>S</sub> so	source current	T <sub>sp</sub> = 25 °C		-	11	А
		T <sub>amb</sub> = 25 °C	[1]	-	2	А
I <sub>SM</sub>	peak source current	single pulse; $t_p \le 10 \ \mu s$ ; $T_{sp} = 25 \ ^{\circ}C$		-	44	А
ESD maximu	m rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	2000	V
Avalanche ru	iggedness		·			
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 0.5 A; DUT in v avalanche (unclamped)		-	15	mJ

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
 Measured between all pins.



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#### 60 V, N-channel Trench MOSFET

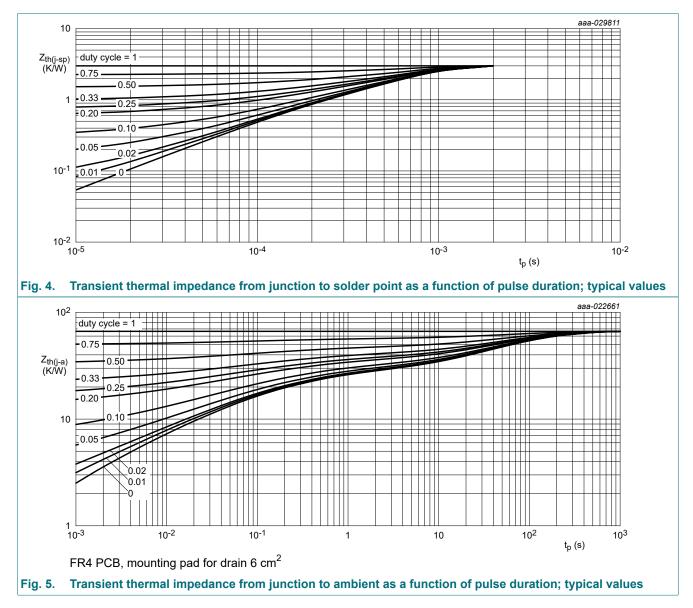


BUK6D56-60E

## 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	66	76	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

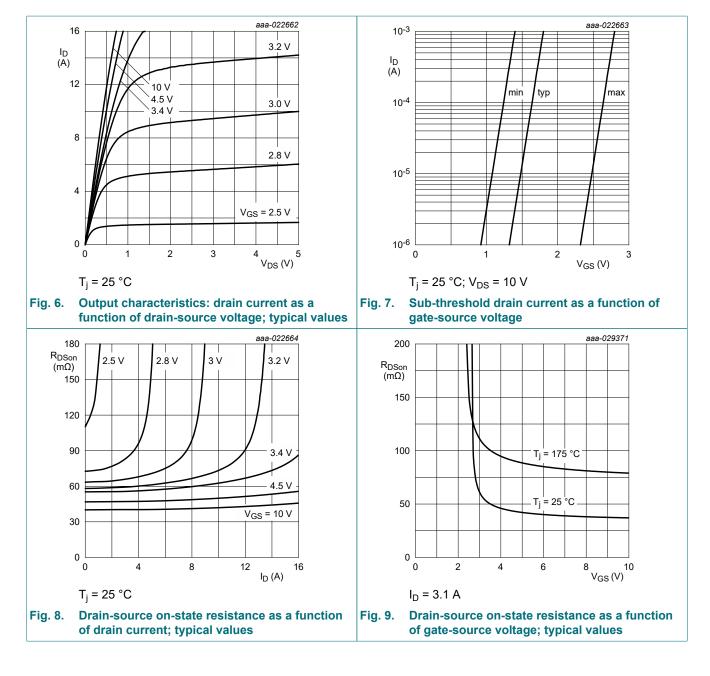
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



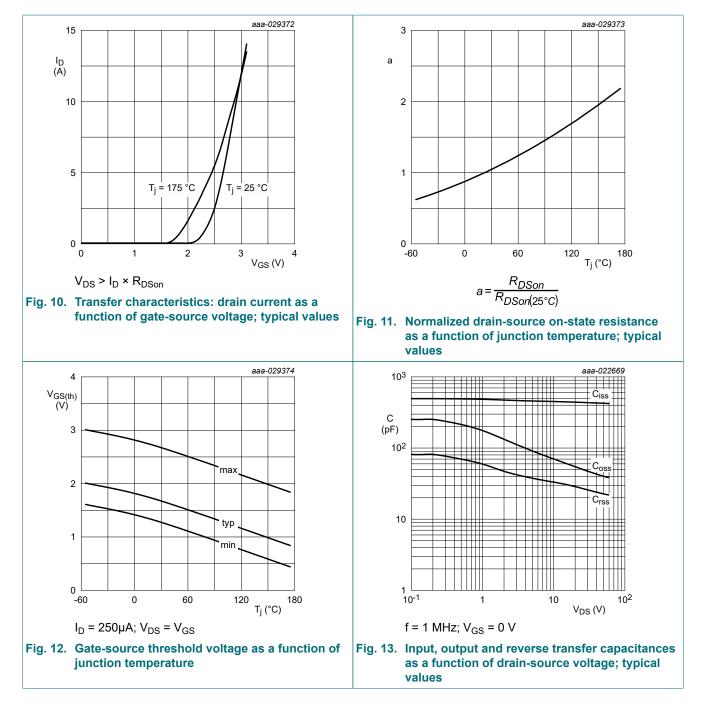
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	60	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$	1.3	1.7	2.7	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	20	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
Doon	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4 A; T <sub>j</sub> = 25 °C	-	42	56	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4 A; T <sub>j</sub> = 175 °C	-	91	122	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.6 A; T <sub>j</sub> = 25 °C	-	48	69	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 4 A; T <sub>j</sub> = 25 °C	-	17	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	aracteristics		l			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 4 A; V <sub>GS</sub> = 10 V;	-	7.5	12	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	1.2	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	435	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	47	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	26	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; I <sub>D</sub> = 4 A; V <sub>GS</sub> = 10 V;	-	4.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	13.5	-	ns
t <sub>f</sub>	fall time		-	7	-	ns
Source-drai	n diode	· · · · ·				
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 2 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 1.4 A; dI <sub>S</sub> /dt = -100 A/μs;	-	13	-	ns
Qr	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	-	6	-	nC

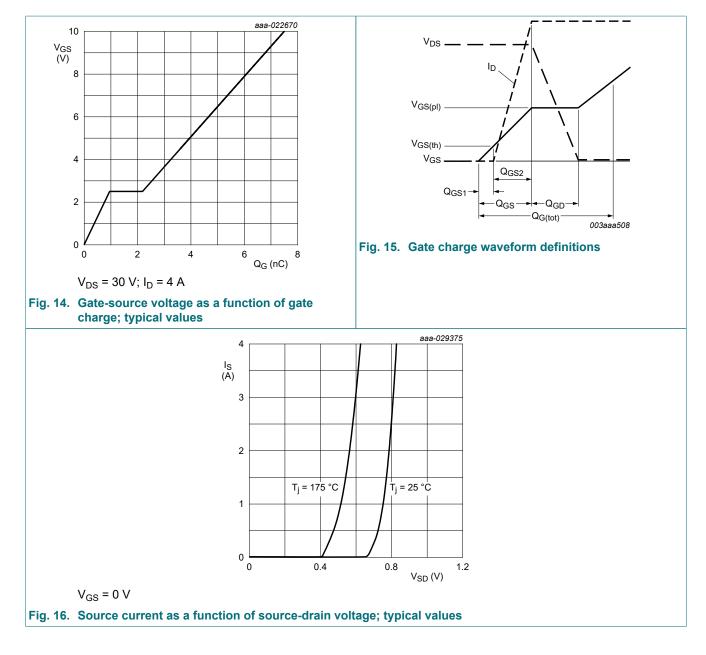
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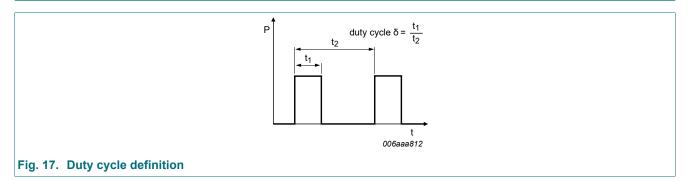


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# **11. Test information**

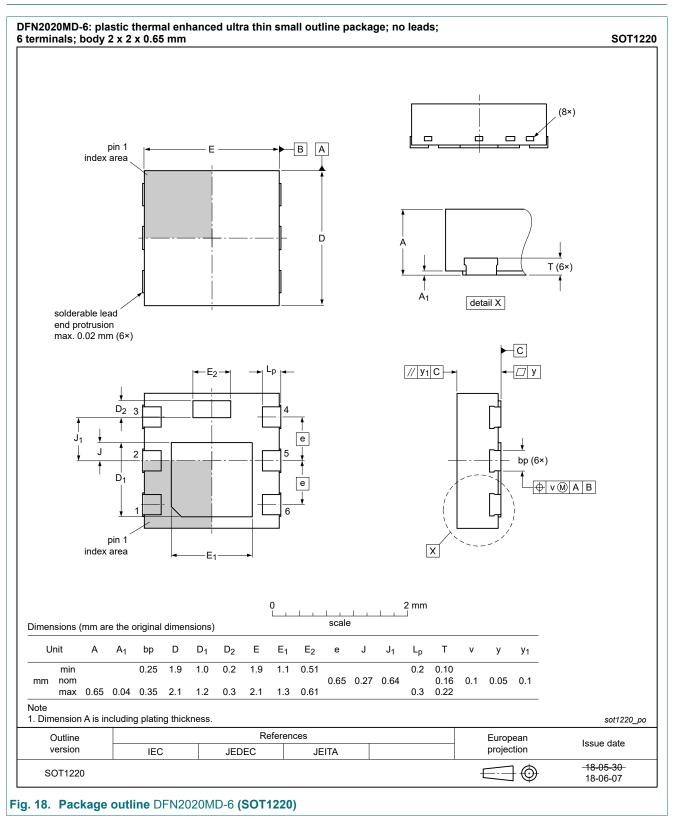


### **Quality information**

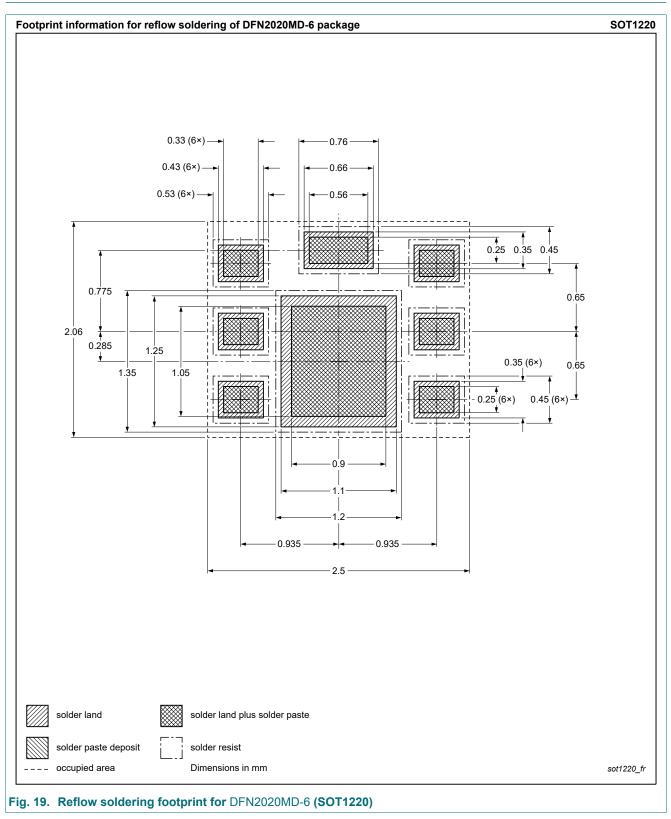
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

BUK6D56-60E

## 12. Package outline



## 13. Soldering



# 14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
BUK6D56-60E v.1	20190403	Product data sheet	-	-	

BUK6D56-60E

# 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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